

# **BUK7207-30B**

# N-channel TrenchMOS standard level FET

Rev. 3 — 23 February 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

#### 1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol                 | Parameter                              | Conditions  |     | Min | Тур | Max | Unit |
|------------------------|--|---|-----|-----|-----|-----|------|
| $V_{DS}$               | drain-source<br>voltage                | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 185 °C   |     | -   | -   | 30  | V    |
| I <sub>D</sub>         | drain current                          | $V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C};$<br>see <u>Figure 1</u> ; see <u>Figure 3</u>  | [1] | -   | -   | 75  | Α    |
| P <sub>tot</sub>       | total power<br>dissipation             | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  |     | -   | -   | 167 | W    |
| Static characteristics |  |   |     |     |     |     |      |
| R <sub>DSon</sub>      | drain-source<br>on-state<br>resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{Figure 12}};$<br>see $\frac{\text{Figure 12}}{\text{Figure 12}}$ |     | -   | 5.9 | 7   | mΩ   |



#### N-channel TrenchMOS standard level FET

Table 1. Quick reference data ...continued

| Symbol               | Parameter  | Conditions   | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| Avalanche            | ruggedness   |  |     |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source<br>avalanche energy | $I_D = 75 \text{ A}; V_{sup} \le 30 \text{ V};$<br>$R_{GS} = 50 \Omega; V_{GS} = 10 \text{ V};$<br>$T_{j(init)} = 25 ^{\circ}C; \text{ unclamped}$ | -   | -   | 329 | mJ   |
| Dynamic c            | Dynamic characteristics                            |  |     |     |     |      |
| $Q_{GD}$             | gate-drain charge                                  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$<br>$V_{DS} = 24 \text{ V}; T_j = 25 ^{\circ}\text{C};$<br>see Figure 13                               | -   | 10  | -   | nC   |

<sup>[1]</sup> Continuous current is limited by package.

# 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1   | G      | gate                              |                    | _              |
| 2   | D      | drain[1]                          | mb                 | D              |
| 3   | S      | source                            |                    |                |
| mb  | D      | mounting base; connected to drain | 1 3                | mbb076 S       |
|     |        |                                   | SOT428 (DPAK)      |                |

<sup>[1]</sup> It is not possible to make connection to pin 2.

# 3. Ordering information

Table 3. Ordering information

| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| BUK7207-30B | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |

# 4. Limiting values

Table 4. Limiting values

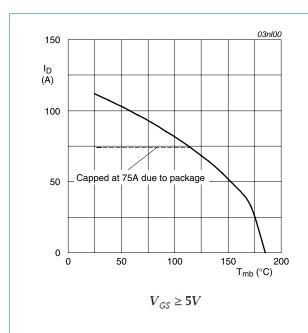
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions  | Min          | Max | Unit |
|----------------------|--|---|--------------|-----|------|
| $V_{DS}$             | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 185 °C   | -            | 30  | V    |
| $V_{DGR}$            | drain-gate voltage                           | $R_{GS} = 20 \text{ k}\Omega$   | -            | 30  | V    |
| $V_{GS}$             | gate-source voltage                          |   | -20          | 20  | V    |
| I <sub>D</sub>       | drain current                                | $V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{see } \frac{\text{Figure 3}}{\text{Figure 3}}};$ | <u>[1]</u> _ | 112 | Α    |
|                      |  | $T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>   | [2] _        | 75  | Α    |
|                      |  | $V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{see } \frac{\text{Figure 3}}{\text{Figure 3}}};$ | <u>[2]</u> _ | 75  | Α    |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_j = 25 \text{ °C}$ ; see Figure 3   | -            | 449 | Α    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>  | -            | 167 | W    |
| T <sub>stg</sub>     | storage temperature                          |   | -55          | 185 | °C   |
| Tj                   | junction temperature                         |   | -55          | 185 | °C   |
| Source-drai          | n diode                                      |   |              |     |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C   | [2] _        | 75  | Α    |
|                      |  |   | <u>[1]</u> _ | 112 | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$  | -            | 449 | Α    |
| Avalanche r          | ruggedness                                   |   |              |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $I_D$ = 75 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped                              | -            | 329 | mJ   |
|                      |  |   |              |     |      |

<sup>[1]</sup> Current is limited by power dissipation chip rating.

<sup>[2]</sup> Continuous current is limited by package.

03no96

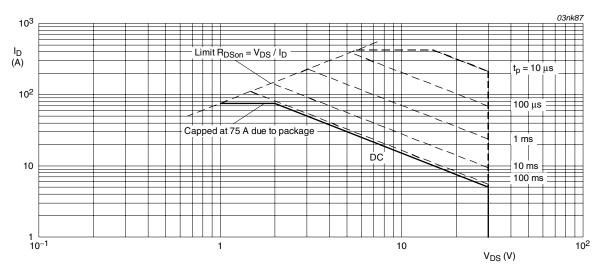


 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$ 

120

Fig 1. Normalized continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



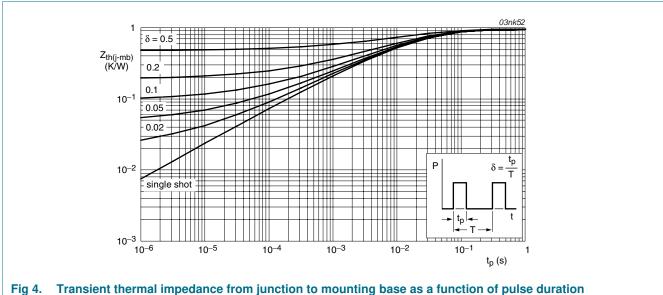
 $T_{mb} = 25$ °C;  $I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol               | Parameter   | Conditions   | Min | Тур  | Max  | Unit |
|----------------------|---|--------------|-----|------|------|------|
| $R_{th(j-mb)}$       | thermal resistance from junction to mounting base | see Figure 4 | -   | -    | 0.95 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient       |              | -   | 71.4 | -    | K/W  |



rig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 6. Characteristics

Table 6. Characteristics

| Table 6.            | Characteristics                  |   |     |      |      |      |
|---------------------|----------------------------------|---|-----|------|------|------|
| Symbol              | Parameter                        | Conditions  | Min | Тур  | Max  | Unit |
| Static cha          | racteristics                     |   |     |      |      |      |
| $V_{(BR)DSS}$       | drain-source                     | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$  | 30  | -    | -    | V    |
|                     | breakdown voltage                | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$   | 27  | -    | -    | V    |
| $V_{GS(th)}$        | gate-source threshold voltage    | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 10  | 2   | 3    | 4    | V    |
|                     |                                  | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 185 °C; see <u>Figure 10</u>  | 0.9 | -    | -    | V    |
|                     |                                  | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 10</u>  | -   | -    | 4.4  | V    |
| I <sub>DSS</sub>    | drain leakage current            | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 185 \text{ °C}$   | -   | -    | 500  | μΑ   |
|                     |                                  | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$  | -   | 0.02 | 1    | μΑ   |
| I <sub>GSS</sub>    | gate leakage current             | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$  | -   | 2    | 100  | nΑ   |
|                     |                                  | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$   | -   | 2    | 100  | nA   |
| $R_{DSon}$          | drain-source on-state resistance | $V_{GS} = 10 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $T_j = 185 ^{\circ}\text{C}$ ; see Figure 11; see Figure 12  | -   | -    | 13.3 | mΩ   |
|                     |                                  | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C;<br>see <u>Figure 11</u> ; see <u>Figure 12</u>  | -   | 5.9  | 7    | mΩ   |
| Dynamic             | characteristics                  |   |     |      |      |      |
| Q <sub>G(tot)</sub> | total gate charge                | $I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$<br>$T_j = 25 ^{\circ}\text{C}; \text{see } \frac{\text{Figure } 13}{\text{Figure } 13}$ | -   | 34   | -    | nC   |
| $Q_{GS}$            | gate-source charge               | $I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$<br>$T_j = 25 \text{ °C}; \text{ see Figure } 13$  | -   | 8    | -    | nC   |
| $Q_{GD}$            | gate-drain charge                | $I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$<br>$T_j = 25 ^{\circ}\text{C}; \text{see } \frac{\text{Figure } 13}{\text{Figure } 13}$ | -   | 10   | -    | nC   |
| C <sub>iss</sub>    | input capacitance                | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$   | -   | 1684 | 2245 | pF   |
| C <sub>oss</sub>    | output capacitance               | $T_j = 25 ^{\circ}\text{C}$ ; see Figure 14   | -   | 625  | 750  | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance     |   | -   | 249  | 314  | pF   |
| t <sub>d(on)</sub>  | turn-on delay time               | $V_{DS} = 25 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \Omega; T_j = 25 \text{ °C}$   | -   | 14   | -    | ns   |
| t <sub>r</sub>      | rise time                        | $V_{DS} = 25 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} 10 \Omega; T_j = 25 ^{\circ}\text{C}$   | -   | 85   | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time              | $V_{DS} = 25 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$   | -   | 55   | -    | ns   |
| t <sub>f</sub>      | fall time                        | $R_{G(ext)} = 10 \Omega; T_j = 25 °C$   | -   | 76   | -    | ns   |
| L <sub>D</sub>      | internal drain<br>inductance     | measured from drain to centre of die; $T_j = 25  ^{\circ}\text{C}$  | -   | 2.5  | -    | nΗ   |
| L <sub>S</sub>      | internal source inductance       | measured from source lead to source bond pad; $T_j = 25  ^{\circ}\text{C}$  | -   | 7.5  | -    | nΗ   |

Table 6. Characteristics ... continued

| Symbol          | Parameter             | Conditions   | Min | Тур  | Max | Unit |
|-----------------|-----------------------|--|-----|------|-----|------|
| Source-drai     | n diode               |  |     |      |     |      |
| V <sub>SD</sub> | source-drain voltage  | $I_S = 20 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 15</u> | -   | 0.85 | 1.2 | V    |
| t <sub>rr</sub> | reverse recovery time | $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$                                  | -   | 43   | -   | ns   |
| Q <sub>r</sub>  | recovered charge      | $V_{GS} = -10 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$                         | -   | 20   | -   | nC   |

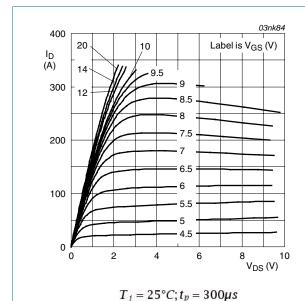


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

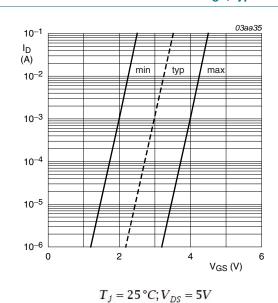
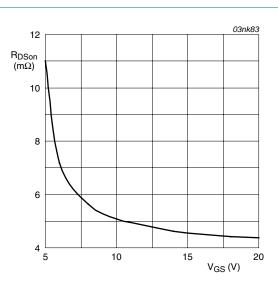
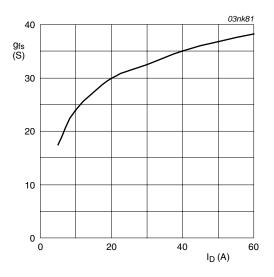


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j=25^{\circ}C; V_{DS}=25V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

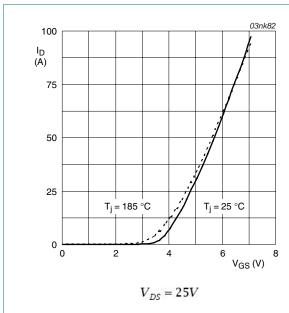


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

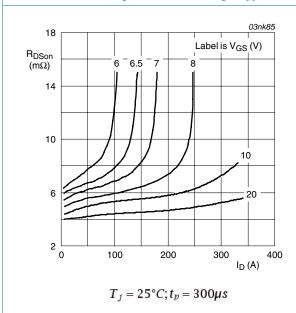


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

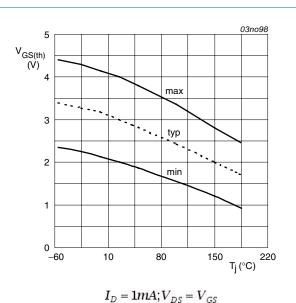


Fig 10. Gate-source threshold voltage as a function of junction temperature

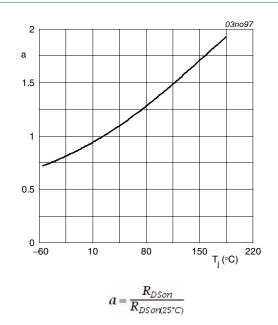


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

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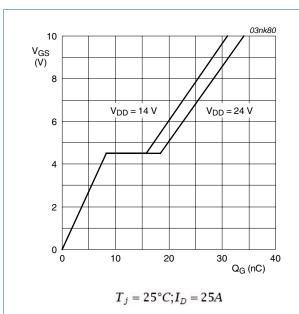
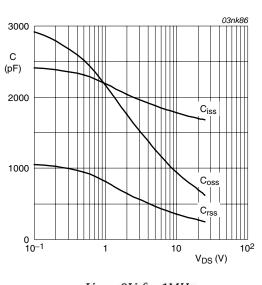


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

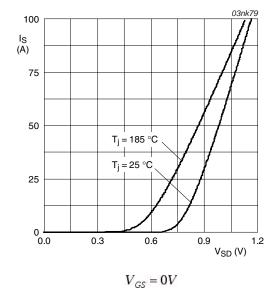


Fig 15. Source current as a function of source-drain voltage; typical values

## 7. Package outline

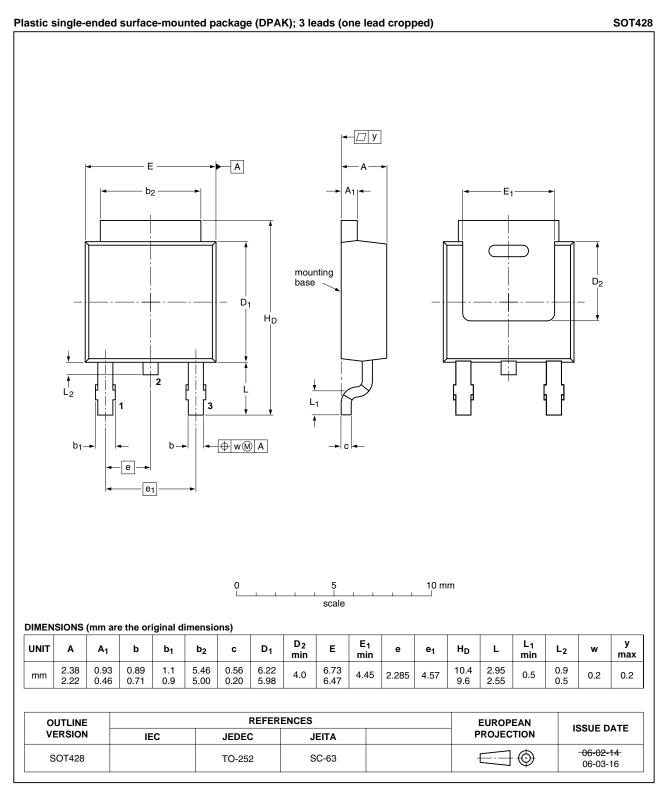


Fig 16. Package outline SOT428 (DPAK)

#### N-channel TrenchMOS standard level FET

# 8. Revision history

#### Table 7. Revision history

| Document ID                        | Release date   | Data sheet status   | Change notice      | Supersedes     |  |
|------------------------------------|--|---|--------------------|----------------|--|
| BUK7207-30B v.3                    | 20110223   | Product data sheet  | -                  | BUK7207_30B-02 |  |
| Modifications:                     | <ul> <li>The format of the of NXP Semicon</li> </ul> | at of this data sheet has been redesigned to comply with the new identity guidelines emiconductors. |                    |                |  |
|                                    | <ul> <li>Legal texts have</li> </ul>                 | e been adapted to the new   | company name where | appropriate.   |  |
| BUK7207_30B-02<br>(9397 750 12227) | 20040122   | Product data  | -                  | BUK7207_30B-01 |  |

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#### 9.1 Data sheet status

| Document status [1] [2]        | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### **Nexperia**

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